

# INFORMATION DISCLOSURE CITATION

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Docket Number (Optional)

SETI-0006

Application Number

Applicant(s)

Fareed et al.

Filing Date

Group Art Unit

## U.S. PATENT DOCUMENTS

| *EXAMINER<br>INITIAL | REF | DOCUMENT NUMBER | DATE    | NAME            | CLASS | SUBCLASS | FILING DATE<br>IF APPROPRIATE |
|----------------------|-----|-----------------|---------|-----------------|-------|----------|-------------------------------|
|                      |     | US006359292B1   | 03-2002 | Sugawara et al. |       |          |                               |
|                      |     | US006316793B1   | 11-2001 | Sheppard et al. |       |          |                               |
|                      |     | US005981977A    | 11-1999 | Furukawa et al. |       |          |                               |
|                      |     | US005851905A    | 12-1998 | McIntosh et al. |       |          |                               |
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## FOREIGN PATENT DOCUMENTS

|  | REF | DOCUMENT NUMBER | DATE | COUNTRY | CLASS | SUBCLASS | Translation |    |
|--|-----|-----------------|------|---------|-------|----------|-------------|----|
|  |     |                 |      |         |       |          | YES         | NO |
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|  |  | "High-Power Microwave GaN/AlGa <sub>N</sub> HEMT's on Semi-Insulating Silicon Carbide Substrates," S. T. Sheppard et al., IEEE Electron Device Letters, Vol. 20, No. 4, April 1999, pp. 161-163. |
|  |  | "High Performance Microwave Power GaN/AlGa <sub>N</sub> MODFETs Grown By RF-Assisted MBE," N.X. Nguyen et al., Electronics Letters, Vol. 36, No. 5, 2nd March 2000, pp. 468-469.                 |

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|                      | "High Electron Mobility Transistor Based on a GaN-AlxGa1-xN Heterojunction," M. Asif Khan et al., Applied Physics Letters, Vol. 63, No. 9, 30 August 1993, pp. 1214-1215.   |
|                      | "AlGaIn/GaN Metal Oxide Semiconductor Heterostructure Field Effect Transistor," M. Asif Khan et al., IEEE Electron Device Letters, Vol. 21, No. 2, February 2000, pp. 63-65.  |
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|                      | "Low Frequency Noise in GaN Metal Semiconductor and Metal Oxide Semiconductor Field Effect Transistors," S. L. Rumyantsev et al., Journal of Applied Physics, Vol. 90, No. 1, 1 July 2001, pp. 310-314.   |
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|                      | "Enhanced Electron Mobility in AlGaIn/InGaIn/AlGaIn Double-Heterostructures by Piezoelectric Effect," Narihiko Maeda et al., Japanese Journal of Applied Physics, Vol. 38, Part 2, No. 7B, 15 July 1999, pp. L799-L801.                             |
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"Energy Band/Lattice Mismatch Engineering in Quaternary AlInGaIn/GaN Heterostructure," M. Asif Khan et al., Phys. Stat, Sol. (a) 176, 227 (1999), pp. 227-230.

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"Piezoelectric Charge Densities in AlGaIn/GaN HFETs," P.M. Asbeck et al., Electronics Letters, Vol. 33, No. 14, 3 July 1997, pp. 1230-1231.

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